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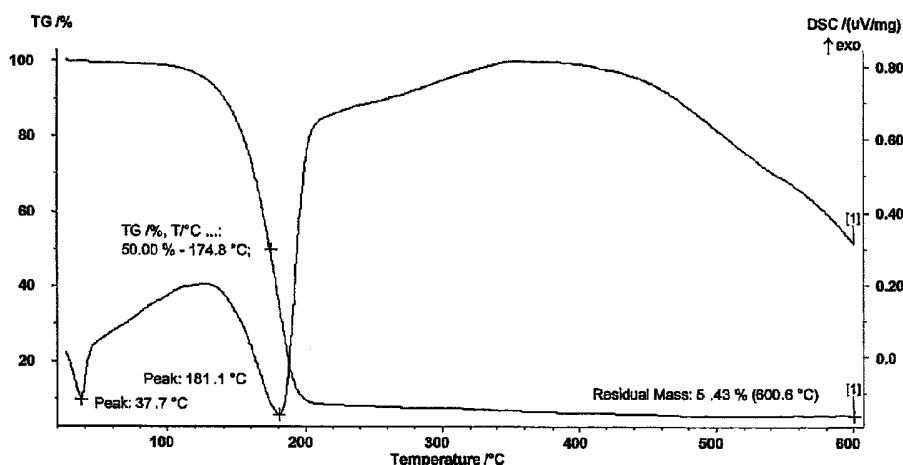
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US 6593484 B2 US 6552209 B1
US 6015917 A

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(54) Abstract Title: Tantalum amide complexes for depositing tantalum-containing films, and method of making same

(57) Tantalum precursors useful in depositing tantalum nitride or tantalum oxides materials on substrates, by processes such as chemical vapor deposition and atomic layer deposition. The precursors are useful in forming tantalum-based diffusion barrier layers on microelectronic device structures featuring copper metallization and/or ferroelectric thin films.



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